IN THE CLAIMS

This listing of claims replaces all prior versions and listings of the claims in the abovereferenced application.

- (Withdrawn) A structure comprising:
- a semiconductor light emitting device comprising a light emitting layer disposed between an n-type region and a p-type region, the light emitting layer configured to emit light of a first wavelength; and
- a cerium-doped garnet phosphor having a cerium concentration between about 4 mol% and about 8 mol%.
- (Withdrawn) The structure of claim 1 wherein the cerium-doped garnet phosphor has a cerium concentration of about 6 mol%.
- 3. (Withdrawn) The structure of claim 1 wherein the cerium-doped gamet phosphor is $(Lu_{1,x,y-a-b}Y_xGd_y)_3(Al_{1,z}Ga_z)_2O_{12}$: Ce_aPr_b wherein 0 < x < 1, 0 < y < 1, $0 < z \le 0.1$, $0 < x \le 0.1$, 0 < x
- 4. (Withdrawn) The structure of claim 1 wherein the cerium-doped garnet phosphor is $Y_3Al_5O_{12}$: Ce^{3+} .
- (Withdrawn) The structure of claim 1 wherein the cerium-doped garnet phosphor is disposed to absorb light of the first wavelength and capable of absorbing light of the first wavelength and emitting light of a second wavelength.
- (Withdrawn) The structure of claim 5 wherein the first wavelength is blue and the second wavelength ranges from green to yellow.
- 7. (Withdrawn) The structure of claim 5 wherein the cerium-doped garnet phosphor is a first wavelength converting material, the structure further comprising a second wavelength-converting material, wherein the second wavelength-converting material is capable of absorbing light of one of the first wavelength and the second wavelength and emitting light of a third wavelength longer than the second wavelength.
 - 8. (Withdrawn) The structure of claim 7 wherein the third wavelength is red.
- 9. (Withdrawn) The structure of claim 7 wherein the second wavelength converting material is one of $(Ca_{1:x}Sr_x)S:Eu^{2+}$ wherein $0 < x \le 1$; $CaS:Eu^{2+}$; $SrS:Eu^{2+}$; $(Sr_{1:x-y}Ba_xCa_y)_{2:x}Si_{5:a}Al_aN_{8:a}O_a:Eu_z^{2+}$ wherein $0 \le a < 5$, $0 < x \le 1$, $0 \le y \le 1$, and $0 < z \le 1$; and $Sr_xSi_xN_a:Eu^{2+}$.

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- (Withdrawn) The structure of claim 1 wherein the semiconductor light emitting device is a III-nitride light emitting diode.
- (Withdrawn) The structure of claim 1 wherein the cerium-doped garnet phosphor is coated on a top surface and a side surface of the light emitting device.
 - 12. (Withdrawn) The structure of claim 1 further comprising: a pair of leads electrically connected to the light emitting device; and a lens disposed over the light emitting device.
- (Withdrawn) The structure of claim 12 wherein the cerium-doped garnet phosphor is dispersed in an encapsulant disposed between the light emitting device and the lens.
- (Withdrawn) The structure of claim 1 wherein the cerium-doped garnet phosphor is spaced apart from the light emitting device.
 - 15. (Previously Presented) A method comprising:

providing a semiconductor light emitting device comprising a light emitting layer disposed between an n-type region and a p-type region, wherein the light emitting layer is configured to emit light of a first wavelength; and

selecting a cerium concentration in a cerium-doped garnet phosphor such that the phosphor has a broader excitation spectrum than 2 mol% cerium Y₃Al₅O₁₂:Ce³⁺; and disposing the phosphor in a path of light emitted by the light emitting device.

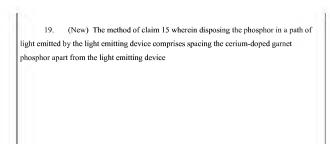
- 16. (Previously Presented) The method of claim 15 wherein selecting a cerium concentration comprises selecting a cerium concentration between about 4 mol% and about 8 mol%.
 - 17. (New) The method of claim 15 wherein:

the cerium-doped gamet phosphor is a first wavelength converting material, the first wavelength converting material being configured to absorb light of the first wavelength and emit light of a second wavelength; and

the structure further comprises a second wavelength-converting material disposed in a path of light emitted by the light emitting device, wherein the second wavelength-converting material is configured to absorb light of one of the first wavelength and the second wavelength and emit light of a third wavelength longer than the second wavelength.

18. (New) The method of claim 17 wherein the second wavelength-converting material is one of $(Ca_{1:x}Sr_x)S:Eu^{2+}$ wherein $0 \le x \le 1$; $CaS:Eu^{2+}$; $SrS:Eu^{2+}$; $(Sr_{1:x:y}Ba_xCa_y)_2$. $Si_{3:x:y}Al_Nc_xO_x:Eu^{2+}$ wherein $0 \le a \le 5$. $0 \le x \le 1$, $0 \le y \le 1$, and $0 \le z \le 1$; and $SrSi:Nx:Eu^{2+}$.

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